Product data sheet

1. General description

Silicon Carbide Schottky diode in a SOD59A (TO-220AC) plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom/Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED/OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------------|---------------------------------|--|--|-----|-----|-----|------|
| V _{RRM} | repetitive peak reverse voltage | | | - | - | 650 | V |
| I _{F(AV)} | average forward current | δ = 0.5; T _{mb} \leq 124 °C; square-wave pulse; Fig. 1; Fig. 2 | | - | - | 6 | А |
| Tj | junction temperature | | | - | - | 175 | °C |
| Static characteristics | | | | | | | |
| V _F | forward voltage | I _F = 6 A; T _j = 25 °C; <u>Fig. 4</u> | | - | 1.5 | 1.7 | V |





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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------------|------------------|---|--|-----|-----|-----|------|
| Dynamic characteristics | | | | | | | |
| Q _r | recovered charge | $I_F = 6 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; | | - | 10 | - | nC |
| | | T _j = 25 °C; <u>Fig. 5</u> | | | | | |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|--------------------|----------------|
| 1 | K | cathode | mb | K — A |
| 2 | Α | anode | 7 0 5 | 001aaa020 |
| mb | mb | mounting base; connected to cathode | TO-220AC (SOD59A) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|----------|--|---------|
| | Name | Description | Version |
| NXPSC06650 | TO-220AC | Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC | SOD59A |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| NXPSC06650 | NXPSC06650 |

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|-------------------------------------|---|-----|-----|------|
| V_{RRM} | repetitive peak reverse voltage | | - | 650 | V |
| V_{RWM} | crest working reverse voltage | | - | 650 | V |
| V _R | reverse voltage | DC | - | 650 | V |
| I _{F(AV)} | average forward current | $δ$ = 0.5; T_{mb} ≤ 124 °C; square-wave pulse; Fig. 1; Fig. 2 | - | 6 | А |
| I _{FRM} | repetitive peak forward current | δ = 0.5; t _p = 25 μs; T _{mb} ≤ 124 °C; square-wave pulse | - | 12 | А |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | - | 36 | А |
| | | t_p = 10 μ s; $T_{j(init)}$ = 25 °C; square-wave pulse | - | 310 | А |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | - | 175 | °C |

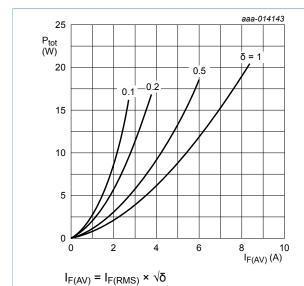


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

 V_o = 0.766 V; R_s = 0.196 Ω

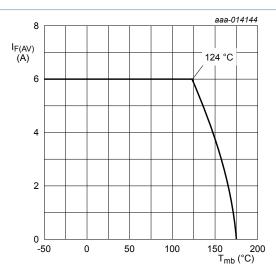


Fig. 2. Forward current as a function of mounting base temperature; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|-------------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 3 | - | - | 2.7 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |

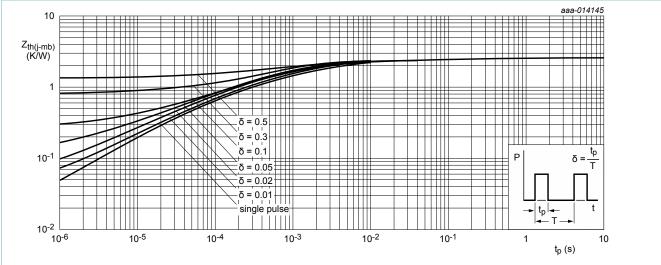


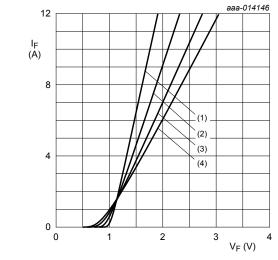
Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|-------------------|--|-----|-----|-----|------|
| Static char | racteristics | | ' | | | _ |
| V_{F} | forward voltage | I _F = 6 A; T _j = 25 °C; <u>Fig. 4</u> | - | 1.5 | 1.7 | V |
| | | I _F = 6 A; T _j = 150 °C; <u>Fig. 4</u> | - | 1.8 | 2.1 | V |
| I _R | reverse current | V _R = 650 V; T _j = 25 °C | - | - | 200 | μA |
| | | V _R = 650 V; T _j = 150 °C | - | - | 640 | μA |
| Dynamic c | haracteristics | | | | | |
| Q _r | recovered charge | $I_F = 6 \text{ A}; dI_F/dt = 500 \text{ A/}\mu\text{s}; V_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 5}}$ | - | 10 | - | nC |
| C _d | diode capacitance | f = 1 MHz; V _R = 1 V; T _j = 25 °C | - | 190 | - | pF |
| | | f = 1 MHz; V _R = 300 V; T _j = 25 °C | - | 23 | - | pF |
| | | f = 1 MHz; V _R = 600 V; T _j = 25 °C | - | 19 | - | pF |



 V_o = 0.766 V; R_s = 0.196 Ω

(1) T_i = 25 °C; typical values

(2) T_i = 100 °C; typical values

(3) $T_j = 150$ °C; typical values

(4) T_j = 175 °C; typical values

Fig. 4. Forward current as a function of forward voltage; typical values

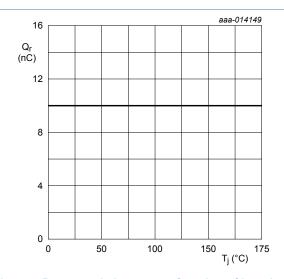
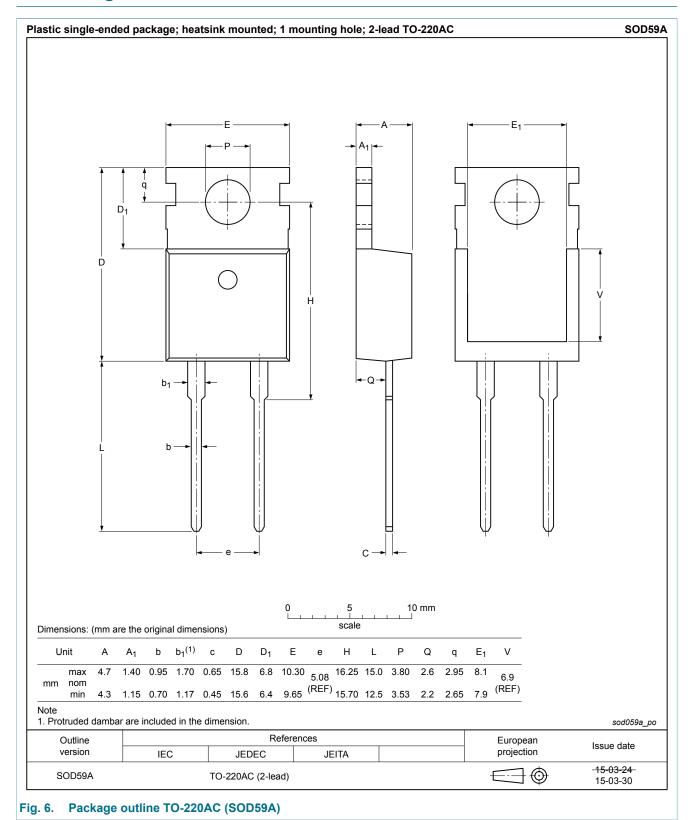


Fig. 5. Recovered charge as a function of junction temperature

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11. Package outline



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12. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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